L Number	Hits	Search Text	DB	Time stamp
1	23	(capacitor near3 within NEAR3 trench near3 substrate) and polysilicon same silicide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/18 14:30
-	4	"6399515"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/15 15:13
-	0	forming and trench and semiconductor and substrate and (first adj (dielectric adj layer)) and pattern$3 and polysilicon and on and (metal adj silicide) and (second adj dielectric adj layer) and over and conductive and hardmask and etching and partially and (dry adj etch) and (wet adj etch) and process	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/15 12:21
-	0	forming and trench and semiconductor and substrate and first and (dielectric adj layer) and pattern$3 and polysilicon and on and (metal adj silicide) and second and over and conductive and hardmask and etch$3 and (dry adj etch) and (wet adj etch) and process	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/15 12:22
-	0	forming and trench and semiconductor and substrate and first and (dielectric adj layer) and pattern$3 and polysilicon and on and (metal adj silicide) and second and over and conductive and hardmask and etch$3 and dry and wet and process	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/15 12:24
-	0	forming and trench and semiconductor and substrate and first and (dielectric adj layer) and pattern$3 and polysilicon and on and (metal adj silicide) and over and conductive and hardmask and etch$3 and dry and wet and process	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/15 12:24
-	26	forming and trench and semiconductor and substrate and first and (dielectric adj layer) and pattern$3 and polysilicon and (metal adj silicide) and conductive and hardmask and etch$3 and dry and wet and process	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/15 13:56
-	20	(forming and trench and semiconductor and substrate and first and (dielectric adj layer) and pattern$3 and polysilicon and (metal adj silicide) and conductive and hardmask and etch$3 and dry and wet and process) and capacitor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/15 12:36
-	18	(forming and trench and semiconductor and substrate and first and (dielectric adj layer) and pattern$3 and polysilicon and (metal adj silicide) and conductive and hardmask and etch$3 and dry and wet and process) and capacitor.clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/15 12:36
-	4	((forming and trench and semiconductor and substrate and first and (dielectric adj layer) and pattern$3 and polysilicon and (metal adj silicide) and conductive and hardmask and etch$3 and dry and wet and process) and capacitor.clm.) and hardmask.clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/15 12:36

-	0	forming and trench.clm. and semiconductor and substrate and first and (dielectric adj layer) and pattern$3 and polysilicon and (metal adj silicide) and conductive and hardmask and etch$3 and dry and wet and process	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/15 13:20
-	349	438/704.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/15 13:20
-	32	forming and semiconductor and substrate and first and (dielectric adj layer) and pattern$3 and polysilicon and (metal adj silicide) and conductive and hardmask and etch$3 and dry and wet and process	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/15 13:20
-	30	(forming and semiconductor and substrate and first and (dielectric adj layer) and pattern$3 and polysilicon and (metal adj silicide) and conductive and hardmask and etch$3 and dry and wet and process) and 438/$5.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/15 13:21
-	2	((forming and semiconductor and substrate and first and (dielectric adj layer) and pattern$3 and polysilicon and (metal adj silicide) and conductive and hardmask and etch$3 and dry and wet and process) and 438/$5.ccls.) and 438/704.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/15 14:49
-	1	"4676866".PN.	USPAT	2004/06/15 13:24
-	20	4793896.URPN.	USPAT	2004/06/15 13:25
-	2	438/704.ccls. and (forming and trench and semiconductor and substrate and first and (dielectric adj layer) and pattern$3 and polysilicon and (metal adj silicide) and conductive and hardmask and etch$3 and dry and wet and process)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/15 13:32
-	20	4793896.URPN.	USPAT	2004/06/15 13:33
-	12	(US-4793896-$ or US-6686237-$ or US-6548343-$ or US-6534809-$ or US-5122225-$ or US-6291883-$ or US-5913139-$ or US-4957590-$ or US-4863559-$ or US-6399515-$).did. or (US-20010034106-$).did. or (US-6399515-$).did.	USPAT; US-PGPUB; DERWENT	2004/06/15 13:53
-	0	(438/630 and 438/239 and 438/240 and 257/295 and 438/396 and 438/642 and 257/734 and 438/618 438/669 and 438/709 and 438/734).ccls. and trench and capacitor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/15 13:59
-	2	(forming and trench and semiconductor and substrate and first and (dielectric adj layer) and pattern$3 and polysilicon and (metal adj silicide) and conductive and hardmask and etch$3 and dry and wet and process) and 438/704.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/15 13:57
-	292	438/239.ccls. and trench and capacitor and etch$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/18 14:29
-	155	(438/239.ccls. and trench and capacitor and etch$4) and silicide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/15 14:00

-	10	((438/239.ccls. and trench and capacitor and etch$4) and silicide) and hardmask	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/15 14:00
-	2	((438/239.ccls. and trench and capacitor and etch$4) and silicide) and hardmask.clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/15 14:00
-	4	("6656748" "6713342").pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/15 14:50
-	2	6686237.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/15 15:13
-	1	10/286,936	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/16 05:14